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Hologram Lasers GH5R41HA3C

GH5R41HA3C

(Under development)

■ Features

- (1) High power output (pulse MAX. 144mW)
- (2) For MAX. ×24 speed CD-R, ×40 speed CD-ROM (With built-in MIN. 45MHz OPIC*)
- (3) High coupling efficiency The ellipticity $(\theta \perp / \theta / \ell)$ is close to 1.
- (4) \$\phi 4.8mm\$ thickness package
- (5) With built-in beam splitter and diffraction grating

*OPIC: (Optical IC) is a trademark of SHARP Corporation.

An OPIC consists of a light-detecting element and a signal-processing circuit integrated onto a single chip.

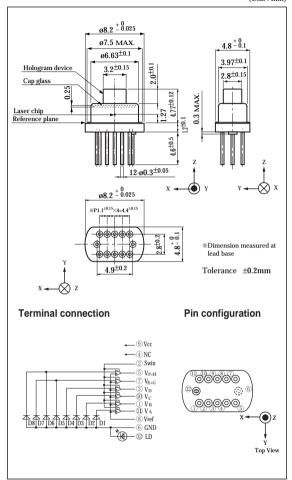
Applications

- (1) CD-R drives
- (2) CD-RW drives

High Power Output Hologram Laser for MAX. ×24 Speed CD-R Drive

Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings

(Tc=25°C)

Parame	eter	Symbol	Rating	Unit
*1 Optical power output	ıt	Рнс	101	mW
*2 Optical power output	ıt (pulse)	РнР	144	mW
Reverse voltage	Laser	VR	2	V
OPIC supply voltage	е	Vcc	6	V
*3 Operating temperat	ure	Topr	0 to +60	°C
*3 Storage temperatur	e	Tstg	-40 to +85	°C
**4 Soldering temperate	ure	Tsold	260	°C

^{*1} Output power from hologram laser Equivalent to 120mW (CW) from cap glass

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Output power from hologram laser Equivalent to 160mW (pulse) from cap glass (Pulse width: 0.5μs, Duty: 50%)

^{*3} Case temperature *4 At the position of 1.6mm from the lead base (Within 5s)

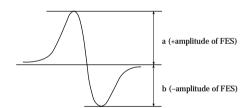
■ Electro-optical Characteristics

 $(Tc=25^{\circ}C)$

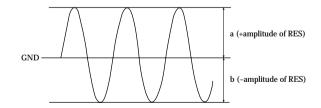
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*1 Focal offset	DEF	Collimated lens output power 1.5mW, High gain	-0.7	-	+0.7	μm
*2 Focal error symmetry	Bres	Collimated lens output power 1.5mW, High gain	-25	-	+25	%
*3 Radial error balance	Bres	Collimated lens output power 1.5mW, High gain	-25	-	+25	%
**4 RF output amplitude	Vrfh	Collimated lens output power 1.5mW, High gain	0.65	0.94	1.23	V
*5 FES output amplitude	VFES	Collimated lens output power 1.5mW, High gain	0.35	0.59	0.94	V
*6 RES output amplitude	Vres	Collimated lens output power 1.5mW, High gain	0.09	0.19	0.3	V
*7 Main spot balance	MSB	Collimated lens output power 1.5mW, High gain	80	(100)	120	%
**8 Sub spot balance	SSB	Collimated lens output power 1.5mW, High gain	80	(100)	120	%
Jitter	JIT	Collimated lens output power 1.5mW, High gain	-	-	23	ns
*9 Strain of RF signal shape	RFh	Collimated lens output power 1.5mW, High gain	-	-	230	%

 $^{^{*1}}$ Distance between FES=0 and jitter minimum point

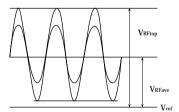
^{**2 (}a-b) / (a+b)







^{*9} VRFtop/VRFave



^{**4} Amplitude of Va+Vb+Vc+Vd (focal servo ON, radial servo ON)

^{*5} VB-VA (Focal vibration)

and its definition of (Vc-V_D)-k1(Ve+g-V_F+H). $k1=(Vc+V_D)/(Ve+g+V_F+H)=1$ When tracking servo is ON, (Vc-V_D)-k1(Ve+g-V_F+H)+ α should be 0.

^{**7} $(V_A+V_B) / (V_C+V_D)$

^{*8} Vc/VD

Electro-optical Characteristics of Laser Diode

 $(Tc=25^{\circ}C)$

Para	meter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Threshold curren	nt		Ith	-	-	30	41	mA
Operating curren	t		Iop	Po=100mW	-	130	155	mA
Operating voltage	e		V_{op}	Po=100mW	-	2.2	2.5	V
Wavelength			λ_{p}	Po=100mW	773	784	797	nm
Differential efficie	Differential efficiency		ηd	70mW I(100mW)-I(30mW)	0.7	0.85	1.2	mW/mA
Stability of differe	Stability of differential efficiency		$\Delta\eta_d$	Po=10 to 150mW	-	-	40	%
II-10:	al -	Parallel	θ//	D 400 W	7.5	9	10.5	۰
Half intensity ang	gie	Perpendicular	θΤ		14.5	17	19.5	۰
Emission	Deviation	Parallel	ø//	Po=100mW	-2	-	+2	۰
characteristics	angle	Perpendicular	ø⊥		-3	-	+3	۰
Beam shift	Beam shift		$\Delta ø //$	ø//(100mW)-ø//(3mW)	-1	-	+1	۰
IZ:l.	77. 1		K-LI1	Po=10 to 150mW	0.988	-	-	%
Kink			K-LI2	P1=30mW, P2=90mW, P3=150mW	-	-	15	%

Electro-optical Characteristics of OPIC for Signal Detection*10

(Tc=25°C, Vcc=5V, Vref=2.1V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	*11 Segment
Supply current	Icc1	High gain, Gain switching SW=H	-	25	32	mA	
	Icc2	Low gain, Gain switching SW=L	-	30	35	mA	
*12 Output offset voltage	Vod	Common to high/low gain, No light	-25	2	+25	mV	A, B
Offset voltage difference, Gain switching	ΔV_{od}	Common to high/low gain	-30	-	+30	mV	A, B

^{*9 0.1}μF or more capacitor should be added between OPIC power supply terminal and GND, Vref terminal and GND. (at the position of 5mm or less from the lead base)

 $A: V_A, V_B, V_C, V_D$

B: VE+G, VF+H

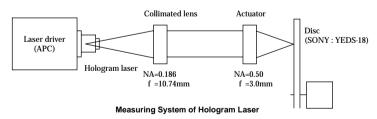
*1

*2

Electro-optical Characteristics of Hologram Laser (Design Standard*)*1

(Tc=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*2 Focal error signal capture range	-	_	-	14	-	μm
Focal error signal sensitivity	-	-	-	13	-	%/µm



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^{*10} Applicable divisions correspond to output terminals .

^{*11} Difference from Vref

^{*} These parameters are not guaranteed performance, but general specifications of each optical element which makes up a hologram laser.

Optical Characteristics of Hologram Device (Design Standard*)

(Tc=25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Hologram diffraction	0 th	-	λ=780nm	77	82	-	%
efficiency	±1st	-	λ=780IIII	6	7	9	%
Hologram diffraction	D1, D2	-	λ=780nm	-	21.1	-	•
angle	Except D1, D2	-	λ=7 80 IIII	-	26.4	-	۰
Grating diffraction effi	ciency	-	0:1	6.7	9	12.4	-
Grating diffraction ang	Grating diffraction angle		λ=780nm	-	2.8	-	۰

Electro-optical Characteristics of Laser Diode (Design Standard*)

(Tc=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	$\Delta \mathbf{x}$		-80	-	+80	μm
Misalignment position	Δy	-	-80	-	+80	μm
	Δz		-80	-	+80	μm
*3 Reflectivity of LD rear facet	$R_{\rm r}$	_	85	-	-	%

Flactro-ontical Characteristics of OPIC for Signal Detection (Design Standard*)

(Ta-95°C Vac-5V V ~ 9 1V)

■ Electro-optical Charac	cteristics	of OPIC for Signal Detection (D	esign Sta	andard*)	(Tc=25°C, Vcc=5V,		, Vref=2.1V)
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	*4 Segment
Supply voltage	Vcc	-	4.75	5	5.25	V	
Reference voltage	Vref	-	2.00	2.1	2.21	V	
Output terminal current	Io	Common to high/low gain	-0.03	0.01	0.3	mA	A, B
Reference voltage terminal current	I_{ref}	Common to high/low gain, No light	-0.5	1	2	mA	
*6,7,8,9 Response frequency	fcm	Main amp, Common to high/low gain, -3dB	45	60	-	MHz	A
Response frequency	fcs	Sub amp, Common to high/low gain, -3dB	1	2	-	MHz	В
*5.8.89Peaking level	$V_{\rm pk}2$	Common to high/low gain f=0.1 to 50MHz	-	-	3	dB	A
*9 Noise level	fnm	Hign gain, 50 Ω end BW=30kHz, f=36MHz	-	-74	-68	dBm	A
Sensitivity 1	R _m 1	Main amp, Hign gain	18	24	30	mV/μW	A
Sensitivity 2	R _m 2	Main amp, Low gain	0.72	0.96	1.2	mV/μW	A
Sensitivity 3	R _m 3	Sub amp, Hign gain	72	96	120	mV/μW	В
Sensitivity 4	R _m 4	Sub amp, Low gain	2.88	3.84	4.8	mV/μW	В
Thermal drift of sensitivity	R _{sm} /T	Common to high/low gain	-	4 200	-	ppm/°C	A, B
Thermal drift of offset voltage	Vod/T	Common to high/low gain, No light	-	300	-	μV/°C	A, B
Thermal drift of offset voltage 1	Vos1/T	Main amp, Hign gain, No light	-	30	-	μV/°C	A
Thermal drift of offset voltage 2	Vos2/T	Main amp, Low gain, No light	-	15	-	μV/°C	A
Thermal drift of offset voltage 3	Vos3/T	Sub amp, Hign gain, No light	-	30	-	μV/°C	В
Thermal drift of offset voltage 4	Vos4/T	Sub amp, Low gain, No light	-	15	-	μV/°C	В
Thermal drift of offset voltage 5	Vos5/T	Between main-sub amp, Hign gain, No light	-	100	-	μV/°C	A-B
Thermal drift of offset voltage 6	Vos6/T	Between main-sub amp, Low gain, No light	-	45	-	μV/°C	A-B
Over/undershoot at gain switching	tstr1	Common to high/low gain, Integral value of the first overshoot/undershoot peak value and overshoot/undershoot time	-	200	-	μs×mV	A, B
Stabilization time at gain switching	tstr2	Common to high/low gain, time for ±3mV	-	-	25	μs	A, B
Settling time	test		-	30	-	ns	A
Maximum output voltage	V₀max	Common to high/low gain, Vref reference	1	-	-	V	A, B

Sampling rate is 1pc./reflection membrane formation process lot

 $10\mu W$ of DC light is applied to the center of each photodiode, and $4\mu W$ of AC light is irradiated. BW=10kHz

* These parameters are not guaranteed performance, but general specifications of each optical element which makes up a hologram laser.

Appricable divisions correspond to output terminals.

A: VA, VB, VC, VD B: VE+G, VF+H

Difference from Vref

Light source is a laser diode of λ =780nm.

⁻³dB level (0dB level is taken for output level when f=0.1MHz)

 $⁵k\Omega$ of resistor and 10pF of capacitor should be connected in parallel between output terminal and Vref terminal.

Please refer to the chapter "Handling Precautions"

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